

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM3K17FU

High Speed Switching Applications

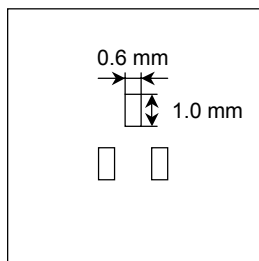
Analog Switch Applications

- Suitable for high-density mounting due to compact package
- High drain-source voltage
- High speed switching

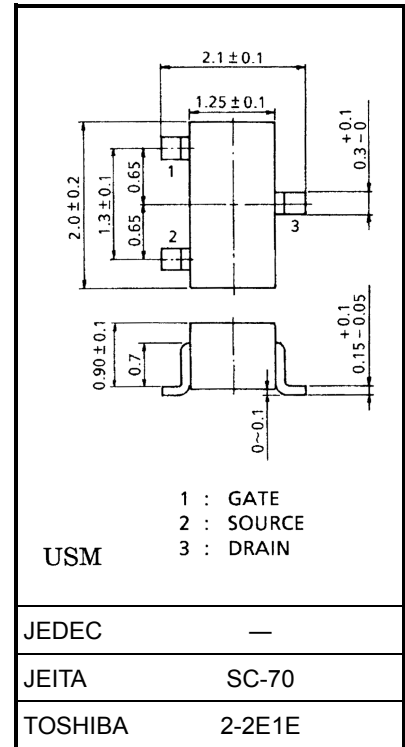
Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain-Source voltage	V_{DS}	50	V
Gate-Source voltage	V_{GSS}	± 7	V
Drain current	DC	I_D	100
	Pulse	I_{DP}	200
Drain power dissipation (Ta = 25°C)	P_D (Note)	150	mW
Channel temperature	T_{ch}	150	°C
Storage temperature range	T_{stg}	-55~150	°C

Note: Mounted on FR4 board
(25.4 mm × 25.4 mm × 1.6 t, Cu Pad: 0.6 mm² × 3)

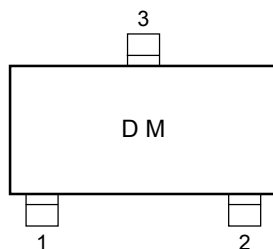


Unit: mm

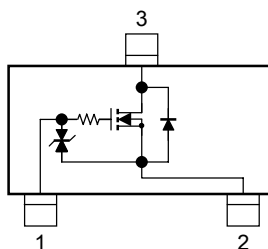


Weight: 6 mg (typ.)

Marking



Equivalent Circuit



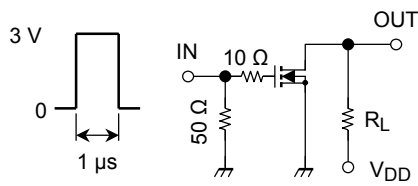
This transistor is an electrostatic sensitive device. Please handle with caution.

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 7\text{ V}, V_{DS} = 0$	—	—	± 5	μA
Drain-Source breakdown voltage	$V_{(BR)DSS}$	$I_D = 0.1\text{ mA}, V_{GS} = 0$	50	—	—	V
Drain cut-off current	I_{DSS}	$V_{DS} = 50\text{ V}, V_{GS} = 0$	—	—	1	μA
Gate threshold voltage	V_{th}	$V_{DS} = 3\text{ V}, I_D = 1\text{ }\mu\text{A}$	0.9	—	1.5	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3\text{ V}, I_D = 10\text{ mA}$	20	40	—	mS
Drain-Source ON resistance	$R_{DS(ON)}$	$I_D = 10\text{ mA}, V_{GS} = 4\text{ V}$	—	12	20	Ω
		$I_D = 10\text{ mA}, V_{GS} = 2.5\text{ V}$	—	22	40	
Input capacitance	C_{iss}	$V_{DS} = 3\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	7	—	pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 3\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	3	—	pF
Output capacitance	C_{oss}	$V_{DS} = 3\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$	—	7	—	pF
Switching time	Turn-on time	t_{on}	—	100	—	ns
	Turn-off time					

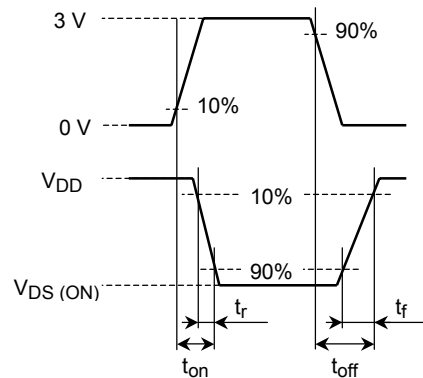
Switching Time Test Circuit

(a) Test circuit

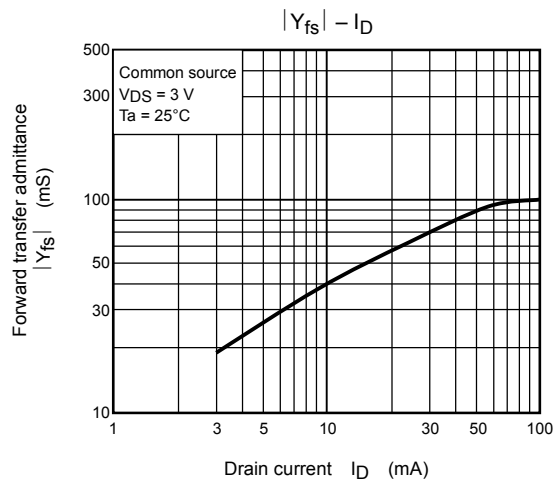
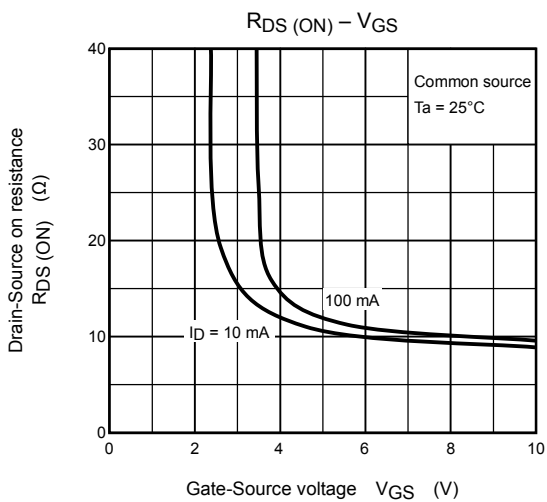
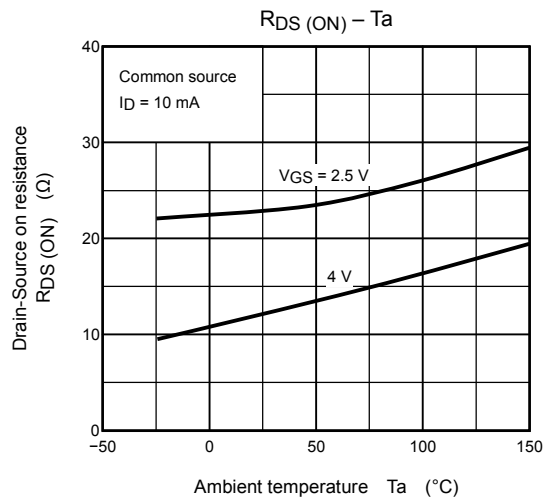
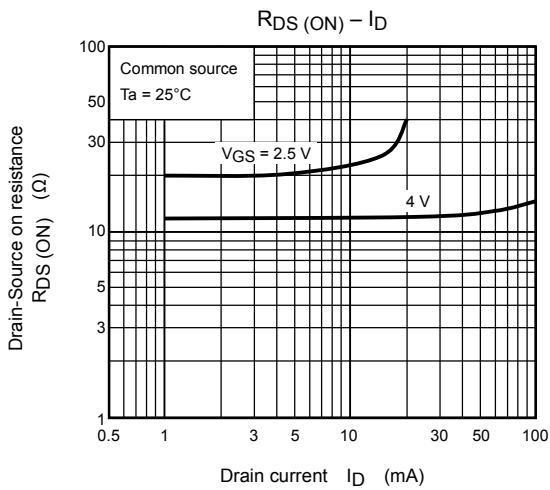
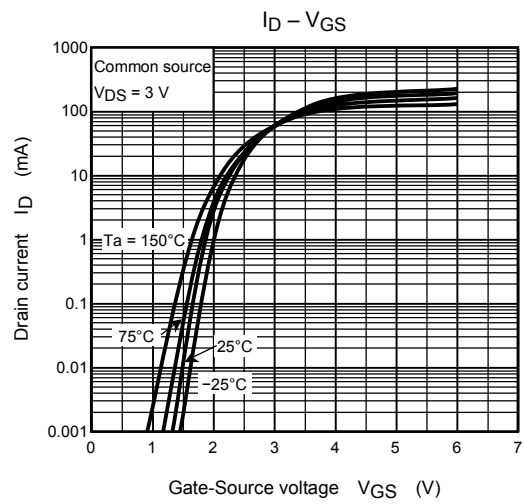
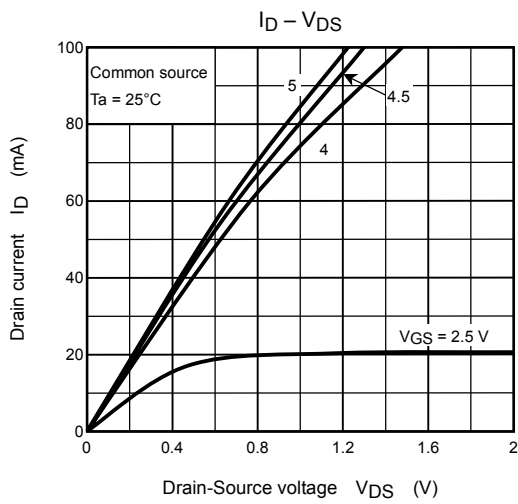


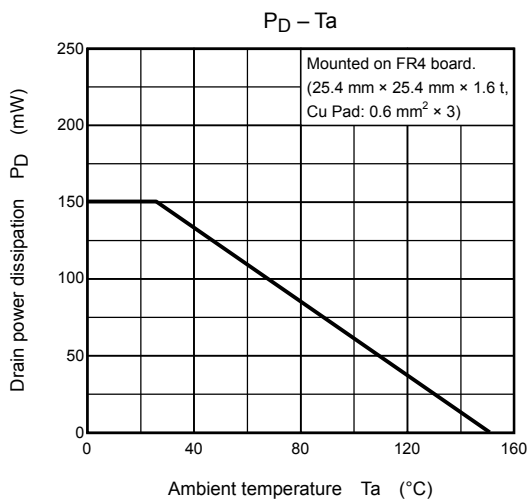
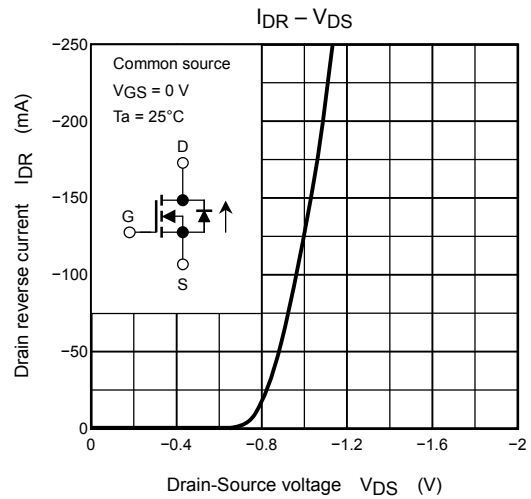
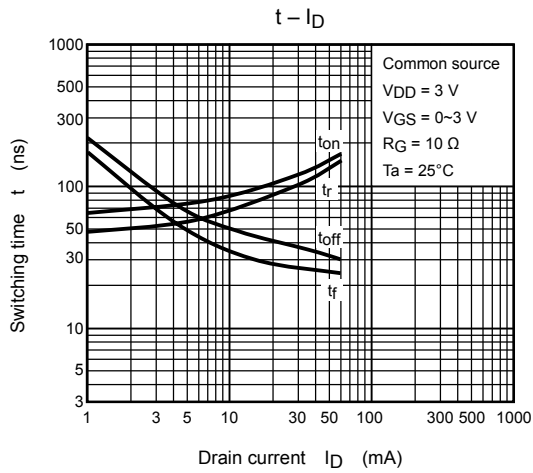
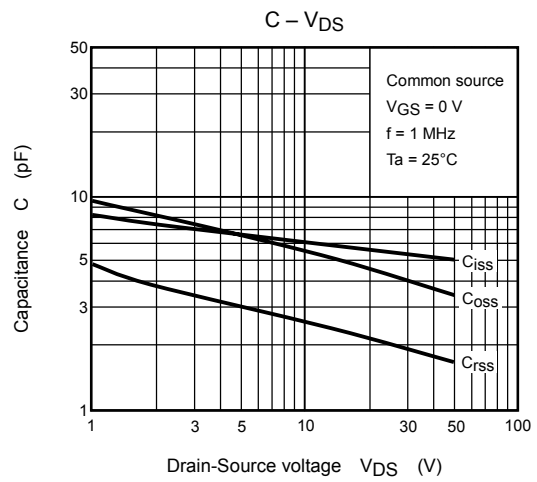
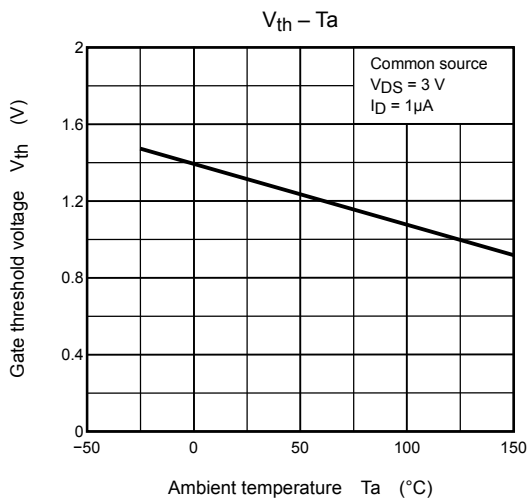
$V_{DD} = 3\text{ V}$
 Duty $\leq 1\%$
 V_{IN} : $t_r, t_f < 5\text{ ns}$
 $(Z_{out} = 50\text{ }\Omega)$
 Common source
 $T_a = 25^\circ\text{C}$

(b) V_{IN}



(c) V_{OUT}





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